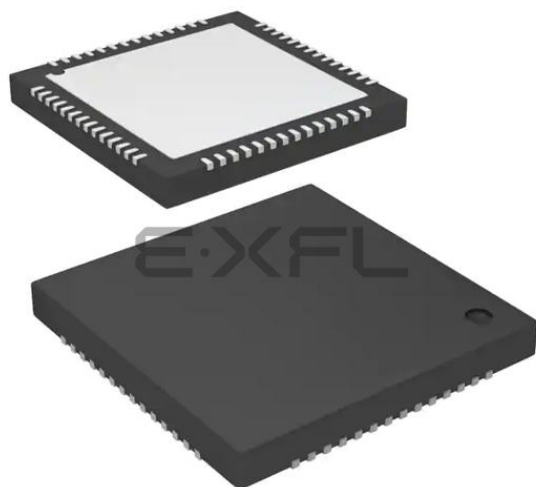




Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	M8C
Core Size	8-Bit
Speed	24MHz
Connectivity	I ² C, SPI, UART/USART, USB
Peripherals	POR, PWM, WDT
Number of I/O	50
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.25V
Data Converters	A/D 47x14b; D/A 2x9b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	56-VFQFN Exposed Pad
Supplier Device Package	56-QFN-EP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c24894-24ltxit

3. More Information

Cypress provides a wealth of data at www.cypress.com to help you to select the right PSoC device for your design, and to help you to quickly and effectively integrate the device into your design. For a comprehensive list of resources, see the knowledge base article [KBA92181, Resources Available for CapSense® Controllers](#). Following is an abbreviated list for CapSense devices:

- Overview: [CapSense Portfolio](#), [CapSense Roadmap](#)
- Product Selectors: [CapSense](#), [CapSense Plus](#), [CapSense Express](#), [PSoC3 with CapSense](#), [PSoC5 with CapSense](#), [PSoC4](#). In addition, [PSoC Designer](#) offers a device selection tool at the time of creating a new project.
- Application notes: Cypress offers CapSense application notes covering a broad range of topics, from basic to advanced level. Recommended application notes for getting started with CapSense are:
 - [AN64846: Getting Started With CapSense](#)
 - [AN2397: CapSense® Data Viewing Tools](#)
- Technical Reference Manual (TRM):
 - [CY8CPLC20](#), [CY8CLED16P01](#), [CY8C29x66](#), [CY8C27x43](#), [CY8C24x94](#), [CY8C24x23](#), [CY8C24x23A](#), [CY8C22x13](#), [CY8C21x34](#), [CY8C21x34B](#), [CY8C21x23](#), [CY7C64215](#), [CY7C603xx](#), [CY8CNP1xx](#), and [CYWUSB6953 PSoC® Programmable System-on-Chip TRM](#)

- Development Kits:
 - [CY3280-24x94 Universal CapSense Controller Board](#) features a predefined control circuitry and plug-in hardware to make prototyping and debugging easy. Programming and I2C-to-USB Bridge hardware are included for tuning and data acquisition.
 - [CY3280-BMM Matrix Button Module Kit](#) consists of eight CapSense sensors organized in a 4x4 matrix format to form 16 physical buttons and eight LEDs. This module connects to any CY3280 Universal CapSense Controller Board, including CY3280-20x66 Universal CapSense Controller.
 - [CY3280-BSM Simple Button Module Kit](#) consists of ten CapSense buttons and ten LEDs. This module connects to any CY3280 Universal CapSense Controller Board, including CY3280-20x66 Universal CapSense Controller.

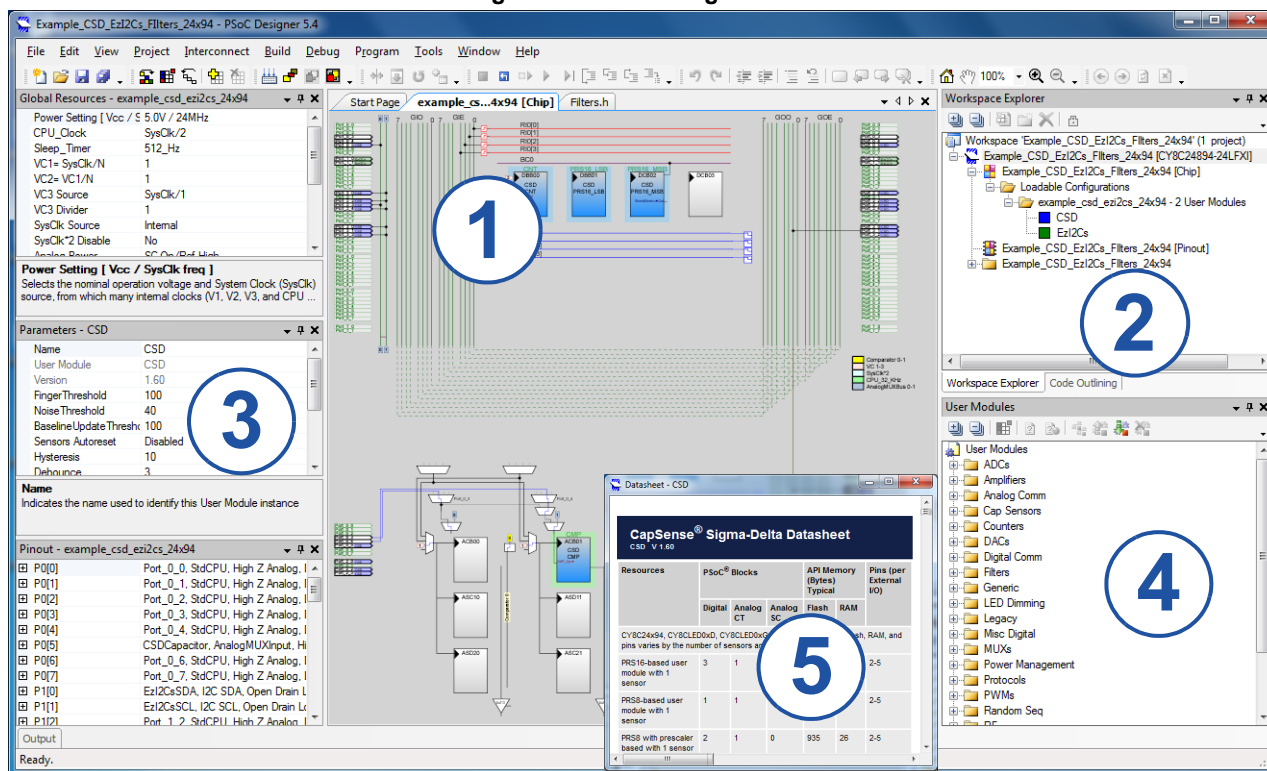
The [CY3217-MiniProg1](#) and [CY8CKIT-002 PSoC® MiniProg3](#) device provides an interface for flash programming.

3.1 PSoC Designer

[PSoC Designer](#) is a free Windows-based Integrated Design Environment (IDE). It enables concurrent hardware and firmware design of systems based on CapSense (see [Figure 1](#)). With PSoC Designer, you can:

1. Drag and drop User Modules to build your hardware system design in the main design workspace
2. Codesign your application firmware with the PSoC hardware, using the PSoC Designer IDE C compiler
3. Configure User Module
4. Explore the library of user modules
5. Review user module datasheets

Figure 1. PSoC Designer Features



Device Programmers	46
Accessories (Emulation and Programming)	47
ORDERING INFORMATION	48
Ordering Code Definitions	48
PACKAGING DIMENSIONS	49
ACRONYMS	54
Acronyms Used	54
DOCUMENT CONVENTIONS	55
Units of Measure	55
Numeric Conventions	55
GLOSSARY	55
ERRATA	60
Part Numbers Affected	60
CY8C24x94 Errata Summary	60
DOCUMENT HISTORY PAGE	64
SALES, SOLUTIONS, AND LEGAL INFORMATION	67
Worldwide Sales and Design Support	67
Products	67
PSoC® Solutions	67
Cypress Developer Community	67
Technical Support	67

5. PSoC Functional Overview

The PSoC family consists of many devices with on-chip controllers. These devices are designed to replace multiple traditional MCU-based system components with one low-cost single-chip programmable component. A PSoC device includes configurable blocks of analog and digital logic, and programmable interconnect. This architecture makes it possible for you to create customized peripheral configurations, to match the requirements of each individual application. Additionally, a fast central processing unit (CPU), flash program memory, SRAM data memory, and configurable I/O are included in a range of convenient pinouts.

The PSoC architecture, shown in “[Logic Block Diagram](#)” on page 1, consists of four main areas: the core, the system resources, the digital system, and the analog system. Configurable global bus resources allow combining all of the device resources into a complete custom system. Each CY8C24x94 PSoC device includes four digital blocks and six analog blocks. Depending on the PSoC package, up to 56 GPIOs are also included. The GPIOs provide access to the global digital and analog interconnects.

5.1 The PSoC Core

The PSoC core is a powerful engine that supports a rich instruction set. It encompasses SRAM for data storage, an interrupt controller, sleep and watchdog timers, and internal main oscillator (IMO) and internal low-speed oscillator (ILO). The CPU core, called the M8C, is a powerful processor with speeds up to 24 MHz. The M8C is a four-million instructions per second (MIPS) 8-bit Harvard-architecture microprocessor.

System resources provide these additional capabilities:

- Digital clocks for increased flexibility
- I²C functionality to implement an I²C master and slave
- An internal voltage reference, multi-master, that provides an absolute value of 1.3 V to a number of PSoC subsystems
- A switch-mode pump (SMP) that generates normal operating voltages from a single battery cell
- Various system resets supported by the M8C

The digital system consists of an array of digital PSoC blocks that may be configured into any number of digital peripherals. The digital blocks are connected to the GPIOs through a series of global buses. These buses can route any signal to any pin, freeing designs from the constraints of a fixed peripheral controller.

The analog system consists of six analog PSoC blocks, supporting comparators, and analog-to-digital conversion up to 10-bits of precision.

5.2 The Digital System

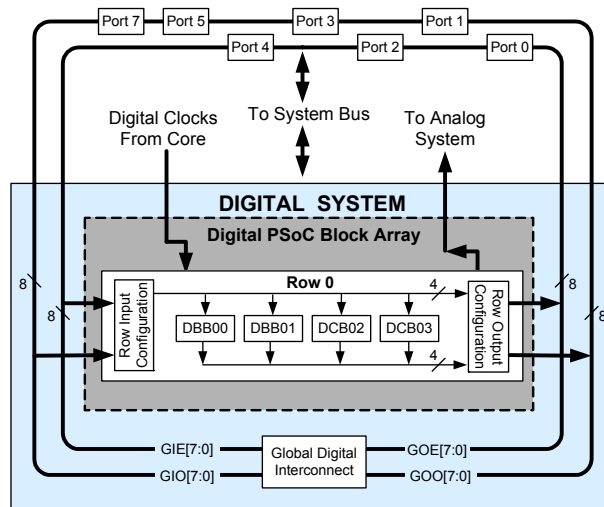
The digital system consists of four digital PSoC blocks. Each block is an 8-bit resource that is used alone or combined with other blocks to form 8-, 16-, 24-, and 32-bit peripherals, which are called user modules. Digital peripheral configurations include:

- PWMs (8- to 32-bit)
- PWMs with dead band (8- to 32-bit)
- Counters (8- to 32-bit)
- Timers (8- to 32-bit)
- UART 8-bit with selectable parity
- SPI master and slave
- I²C slave and multi-master
- CRC/generator (8-bit)
- IrDA
- PRS generators (8- to 32-bit)

The digital blocks are connected to any GPIO through a series of global buses that can route any signal to any pin. The buses also allow for signal multiplexing and for performing logic operations. This configurability frees your designs from the constraints of a fixed peripheral controller.

Digital blocks are provided in rows of four, where the number of blocks varies by PSoC device family. This allows the optimum choice of system resources for your application. Family resources are shown in [Table 1 on page 7](#).

Figure 2. Digital System Block Diagram



9.4 68-Pin Part Pinout (On-Chip Debug)

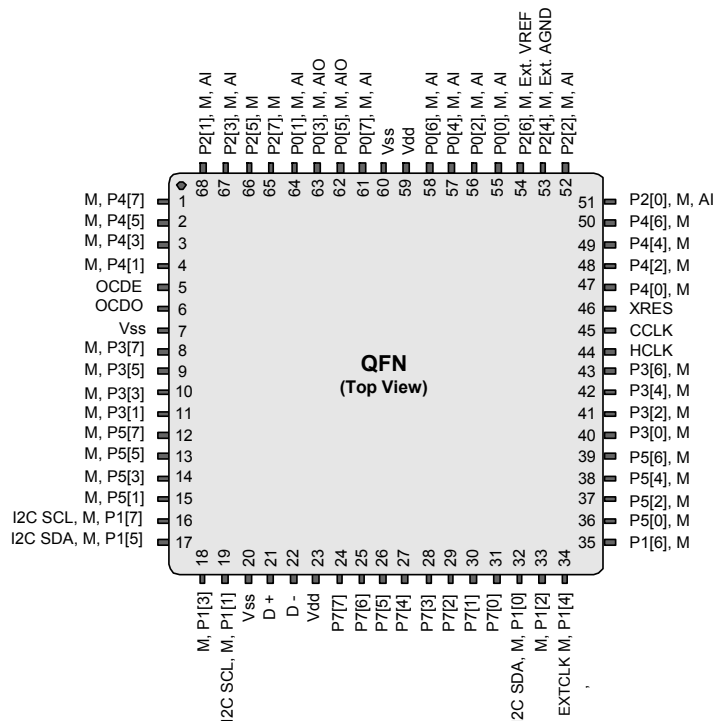
The following 68-pin QFN part table and drawing is for the CY8C24094 OCD PSoC device.

Note This part is only used for in-circuit debugging. It is NOT available for production.

Table 5. 68-Pin Part Pinout (QFN^[12])

Pin No.	Type		Name	Description
	Digital	Analog		
1	I/O	M	P4[7]	
2	I/O	M	P4[5]	
3	I/O	M	P4[3]	
4	I/O	M	P4[1]	
5			OCDE	OCD even data I/O
6			OCDO	OCD odd data output
7	Power		V _{SS}	Ground connection ^[13]
8	I/O	M	P3[7]	
9	I/O	M	P3[5]	
10	I/O	M	P3[3]	
11	I/O	M	P3[1]	
12	I/O	M	P5[7]	
13	I/O	M	P5[5]	
14	I/O	M	P5[3]	
15	I/O	M	P5[1]	
16	I/O	M	P1[7]	I ² C SCL
17	I/O	M	P1[5]	I ² C SDA
18	I/O	M	P1[3]	
19	I/O	M	P1[1]	I ² C SCL, ISSP SCLK ^[14]
20	Power		V _{SS}	Ground connection ^[13]
21	USB		D+	
22	USB		D-	
23	Power		V _{DD}	Supply voltage
24	I/O		P7[7]	
25	I/O		P7[6]	
26	I/O		P7[5]	
27	I/O		P7[4]	
28	I/O		P7[3]	
29	I/O		P7[2]	
30	I/O		P7[1]	
31	I/O		P7[0]	
32	I/O	M	P1[0]	I ² C SDA, ISSP SDATA ^[14]
33	I/O	M	P1[2]	
34	I/O	M	P1[4]	Optional EXTCLK
35	I/O	M	P1[6]	
36	I/O	M	P5[0]	
37	I/O	M	P5[2]	
38	I/O	M	P5[4]	
39	I/O	M	P5[6]	
40	I/O	M	P3[0]	
41	I/O	M	P3[2]	
42	I/O	M	P3[4]	
43	I/O	M	P3[6]	
44			HCLK	OCD high speed clock output
45			CCLK	OCD CPU clock output
46	Input		XRES	Active high pin reset with internal pull-down
47	I/O	M	P4[0]	
48	I/O	M	P4[2]	
49	I/O	M	P4[4]	

Figure 7. CY8C24094 68-Pin OCD PSoC Device



Pin No.	Type		Name	Description
	Digital	Analog		
50	I/O	M	P4[6]	
51	I/O	I, M	P2[0]	Direct switched capacitor block input
52	I/O	I, M	P2[2]	Direct switched capacitor block input
53	I/O	M	P2[4]	External AGND input
54	I/O	M	P2[6]	External VREF input
55	I/O	I, M	P0[0]	Analog column mux input
56	I/O	I, M	P0[2]	Analog column mux input and column output
57	I/O	I, M	P0[4]	Analog column mux input and column output
58	I/O	I, M	P0[6]	Analog column mux input
59	Power		V _{DD}	Supply voltage
60	Power		V _{SS}	Ground connection ^[13]
61	I/O	I, M	P0[7]	Analog column mux input, integration input #1
62	I/O	I/O, M	P0[5]	Analog column mux input and column output, integration input #2
63	I/O	I/O, M	P0[3]	Analog column mux input and column output
64	I/O	I, M	P0[1]	Analog column mux input
65	I/O	M	P2[7]	
66	I/O	M	P2[5]	
67	I/O	I, M	P2[3]	Direct switched capacitor block input
68	I/O	I, M	P2[1]	Direct switched capacitor block input

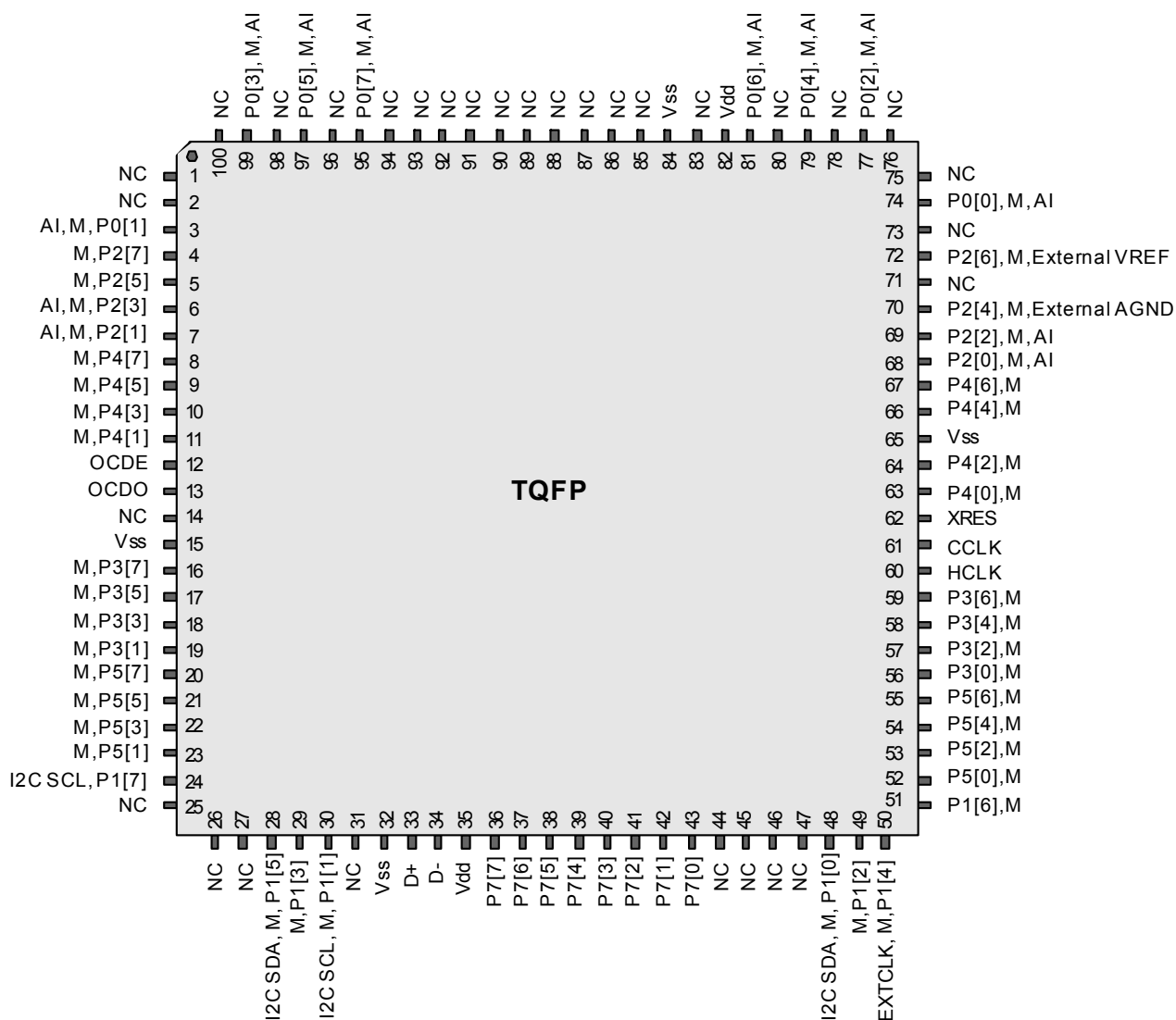
LEGEND A = Analog, I = Input, O = Output, M = Analog Mux Input, OCD = On-Chip Debugger.

Notes

12. The center pad on the QFN package should be connected to ground (V_{SS}) for best mechanical, thermal, and electrical performance. If not connected to ground, it should be electrically floated and not connected to any other signal.

13. All V_{SS} pins should be brought out to one common GND plane.

14. These are the ISSP pins, which are not High Z at POR. See the [PSoC Technical Reference Manual](#) for details.

Figure 10. CY8C24094 OCD (Not for Production)


10.3 Register Map Bank 0 Table: User Space

Name	Addr (0, Hex)	Access	Name	Addr (0, Hex)	Access	Name	Addr (0, Hex)	Access	Name	Addr (0, Hex)	Access
PRT0DR	00	RW	PMA0_DR	40	RW	ASC10CR0	80	RW		C0	
PRT0IE	01	RW	PMA1_DR	41	RW	ASC10CR1	81	RW		C1	
PRT0GS	02	RW	PMA2_DR	42	RW	ASC10CR2	82	RW		C2	
PRT0DM2	03	RW	PMA3_DR	43	RW	ASC10CR3	83	RW		C3	
PRT1DR	04	RW	PMA4_DR	44	RW	ASD11CR0	84	RW		C4	
PRT1IE	05	RW	PMA5_DR	45	RW	ASD11CR1	85	RW		C5	
PRT1GS	06	RW	PMA6_DR	46	RW	ASD11CR2	86	RW		C6	
PRT1DM2	07	RW	PMA7_DR	47	RW	ASD11CR3	87	RW		C7	
PRT2DR	08	RW	USB_SOF0	48	R		88			C8	
PRT2IE	09	RW	USB_SOF1	49	R		89			C9	
PRT2GS	0A	RW	USB_CR0	4A	RW		8A			CA	
PRT2DM2	0B	RW	USB/O_CR0	4B	#		8B			CB	
PRT3DR	0C	RW	USB/O_CR1	4C	RW		8C			CC	
PRT3IE	0D	RW		4D			8D			CD	
PRT3GS	0E	RW	EP1_CNT1	4E	#		8E			CE	
PRT3DM2	0F	RW	EP1_CNT	4F	RW		8F			CF	
PRT4DR	10	RW	EP2_CNT1	50	#	ASD20CR0	90	RW	CUR_PP	D0	RW
PRT4IE	11	RW	EP2_CNT	51	RW	ASD20CR1	91	RW	STK_PP	D1	RW
PRT4GS	12	RW	EP3_CNT1	52	#	ASD20CR2	92	RW		D2	
PRT4DM2	13	RW	EP3_CNT	53	RW	ASD20CR3	93	RW	IDX_PP	D3	RW
PRT5DR	14	RW	EP4_CNT1	54	#	ASC21CR0	94	RW	MVR_PP	D4	RW
PRT5IE	15	RW	EP4_CNT	55	RW	ASC21CR1	95	RW	MVW_PP	D5	RW
PRT5GS	16	RW	EP0_CR	56	#	ASC21CR2	96	RW	I2C_CFG	D6	RW
PRT5DM2	17	RW	EP0_CNT	57	#	ASC21CR3	97	RW	I2C_SCR	D7	#
	18		EP0_DR0	58	RW		98		I2C_DR	D8	RW
	19		EP0_DR1	59	RW		99		I2C_MSCR	D9	#
	1A		EP0_DR2	5A	RW		9A		INT_CLR0	DA	RW
	1B		EP0_DR3	5B	RW		9B		INT_CLR1	DB	RW
PRT7DR	1C	RW	EP0_DR4	5C	RW		9C		INT_CLR2	DC	RW
PRT7IE	1D	RW	EP0_DR5	5D	RW		9D		INT_CLR3	DD	RW
PRT7GS	1E	RW	EP0_DR6	5E	RW		9E		INT_MSK3	DE	RW
PRT7DM2	1F	RW	EP0_DR7	5F	RW		9F		INT_MSK2	DF	RW
DBB00DR0	20	#	AMX_IN	60	RW		A0		INT_MSK0	E0	RW
DBB00DR1	21	W	AMUXCFG	61	RW		A1		INT_MSK1	E1	RW
DBB00DR2	22	RW		62			A2		INT_VC	E2	RC
DBB00CR0	23	#	ARF_CR	63	RW		A3		RES_WDT	E3	W
DBB01DR0	24	#	CMP_CR0	64	#		A4		DEC_DH	E4	RC
DBB01DR1	25	W	ASY_CR	65	#		A5		DEC_DL	E5	RC
DBB01DR2	26	RW	CMP_CR1	66	RW		A6		DEC_CR0	E6	RW
DBB01CR0	27	#		67			A7		DEC_CR1	E7	RW
DCB02DR0	28	#		68		MUL1_X	A8	W	MUL0_X	E8	W
DCB02DR1	29	W		69		MUL1_Y	A9	W	MUL0_Y	E9	W
DCB02DR2	2A	RW		6A		MUL1_DH	AA	R	MUL0_DH	EA	R
DCB02CR0	2B	#		6B		MUL1_DL	AB	R	MUL0_DL	EB	R
DCB03DR0	2C	#	TMP_DR0	6C	RW	ACC1_DR1	AC	RW	ACC0_DR1	EC	RW
DCB03DR1	2D	W	TMP_DR1	6D	RW	ACC1_DR0	AD	RW	ACC0_DR0	ED	RW
DCB03DR2	2E	RW	TMP_DR2	6E	RW	ACC1_DR3	AE	RW	ACC0_DR3	EE	RW
DCB03CR0	2F	#	TMP_DR3	6F	RW	ACC1_DR2	AF	RW	ACC0_DR2	EF	RW
	30		ACB00CR3	70	RW	RDI0RI	B0	RW		F0	
	31		ACB00CR0	71	RW	RDI0SYN	B1	RW		F1	
	32		ACB00CR1	72	RW	RDI0IS	B2	RW		F2	
	33		ACB00CR2	73	RW	RDI0LT0	B3	RW		F3	
	34		ACB01CR3	74	RW	RDI0LT1	B4	RW		F4	
	35		ACB01CR0	75	RW	RDI0RO0	B5	RW		F5	
	36		ACB01CR1	76	RW	RDI0RO1	B6	RW		F6	
	37		ACB01CR2	77	RW		B7		CPU_F	F7	RL
	38			78			B8			F8	
	39			79			B9			F9	
	3A			7A			BA			FA	
	3B			7B			BB			FB	
	3C			7C			BC			FC	
	3D			7D			BD		DAC_D	FD	RW
	3E			7E			BE		CPU_SCR1	FE	#
	3F			7F			BF		CPU_SCR0	FF	#

Blank fields are reserved and should not be accessed.

Access is bit specific.

11.3.6 DC Analog Output Buffer Specifications

The following tables list guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, or 3.0 V to 3.6 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, respectively. Typical parameters are measured at 5 V and 3.3 V at 25°C and are for design guidance only.

Table 17. 5-V DC Analog Output Buffer Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
C_L	Load Capacitance	–	–	200	pF	This specification applies to the external circuit that is being driven by the analog output buffer.
V_{OSOB}	Input offset voltage (absolute value)	–	3	12	mV	
TCV_{OSOB}	Average input offset voltage drift	–	+6	–	$\mu\text{V}/^{\circ}\text{C}$	
V_{CMOB}	Common mode input voltage range	0.5	–	$V_{DD} - 1.0$	V	
R_{OUTOB}	Output resistance					
	Power = low	–	0.6	–	Ω	
	Power = high	–	0.6	–	Ω	
$V_{OHIGHOB}$	High output voltage swing (Load = 32 ohms to $V_{DD}/2$)					
	Power = low	$0.5 \times V_{DD} + 1.1$	–	–	V	
	Power = high	$0.5 \times V_{DD} + 1.1$	–	–	V	
V_{LOWOB}	Low output voltage swing (Load = 32 ohms to $V_{DD}/2$)					
	Power = low	–	–	$0.5 \times V_{DD} - 1.3$	V	
	Power = high	–	–	$0.5 \times V_{DD} - 1.3$	V	
I_{SOB}	Supply current including opamp bias cell					
	(No Load)	–	1.1	5.1	mA	
	Power = low	–	2.6	8.8	mA	
	Power = high					
$PSRR_{OB}$	Supply voltage rejection ratio	53	64	–	dB	$(0.5 \times V_{DD} - 1.3) \leq V_{OUT} \leq (V_{DD} - 2.3)$.

Table 19. 5-V DC Analog Reference Specifications (continued)

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b101	RefPower = high Opamp bias = high	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.218	P2[4] + 1.291	P2[4] + 1.354	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	—
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.335	P2[4] – 1.294	P2[4] – 1.237	V
	RefPower = high Opamp bias = low	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.221	P2[4] + 1.293	P2[4] + 1.358	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	—
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.337	P2[4] – 1.297	P2[4] – 1.243	V
	RefPower = medium Opamp bias = high	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.222	P2[4] + 1.294	P2[4] + 1.360	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	—
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.338	P2[4] – 1.298	P2[4] – 1.245	V
	RefPower = medium Opamp bias = low	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.221	P2[4] + 1.294	P2[4] + 1.362	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	—
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.340	P2[4] – 1.298	P2[4] – 1.245	V
0b110	RefPower = high Opamp bias = high	V _{REFHI}	Ref High	2 × Bandgap	2.513	2.593	2.672	V
		V _{AGND}	AGND	Bandgap	1.264	1.302	1.340	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.008	V _{SS} + 0.038	V
	RefPower = high Opamp bias = low	V _{REFHI}	Ref High	2 × Bandgap	2.514	2.593	2.674	V
		V _{AGND}	AGND	Bandgap	1.264	1.301	1.340	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.005	V _{SS} + 0.028	V
	RefPower = medium Opamp bias = high	V _{REFHI}	Ref High	2 × Bandgap	2.514	2.593	2.676	V
		V _{AGND}	AGND	Bandgap	1.264	1.301	1.340	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.004	V _{SS} + 0.024	V
	RefPower = medium Opamp bias = low	V _{REFHI}	Ref High	2 × Bandgap	2.514	2.593	2.677	V
		V _{AGND}	AGND	Bandgap	1.264	1.300	1.340	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.003	V _{SS} + 0.021	V

Table 20. 3.3-V DC Analog Reference Specifications (continued)

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Unit s
0b010	RefPower = high Opamp bias = high	V _{REFHI}	Ref High	V _{DD}	V _{DD} – 0.119	V _{DD} – 0.005	V _{DD}	V
		V _{AGND}	AGND	V _{DD} /2	V _{DD} /2 – 0.028	V _{DD} /2	V _{DD} /2 + 0.029	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.004	V _{SS} + 0.022	V
	RefPower = high Opamp bias = low	V _{REFHI}	Ref High	V _{DD}	V _{DD} – 0.131	V _{DD} – 0.004	V _{DD}	V
		V _{AGND}	AGND	V _{DD} /2	V _{DD} /2 – 0.028	V _{DD} /2	V _{DD} /2 + 0.028	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.003	V _{SS} + 0.021	V
	RefPower = medium Opamp bias = high	V _{REFHI}	Ref High	V _{DD}	V _{DD} – 0.111	V _{DD} – 0.003	V _{DD}	V
		V _{AGND}	AGND	V _{DD} /2	V _{DD} /2 – 0.029	V _{DD} /2	V _{DD} /2 + 0.028	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.002	V _{SS} + 0.017	V
	RefPower = medium Opamp bias = low	V _{REFHI}	Ref High	V _{DD}	V _{DD} – 0.128	V _{DD} – 0.003	V _{DD}	V
		V _{AGND}	AGND	V _{DD} /2	V _{DD} /2 – 0.029	V _{DD} /2	V _{DD} /2 + 0.029	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.002	V _{SS} + 0.019	V
0b011	All power settings. Not allowed for 3.3 V.	–	–	–	–	–	–	–
0b100	All power settings. Not allowed for 3.3 V.	–	–	–	–	–	–	–
0b101	RefPower = high Opamp bias = high	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.214	P2[4] + 1.291	P2[4] + 1.359	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.335	P2[4] – 1.292	P2[4] – 1.200	V
	RefPower = high Opamp bias = low	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.219	P2[4] + 1.293	P2[4] + 1.357	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.335	P2[4] – 1.295	P2[4] – 1.243	V
	RefPower = medium Opamp bias = high	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.222	P2[4] + 1.294	P2[4] + 1.356	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.337	P2[4] – 1.296	P2[4] – 1.244	V
	RefPower = medium Opamp bias = low	V _{REFHI}	Ref High	P2[4] + Bandgap (P2[4] = V _{DD} /2)	P2[4] + 1.224	P2[4] + 1.295	P2[4] + 1.355	V
		V _{AGND}	AGND	P2[4]	P2[4]	P2[4]	P2[4]	–
		V _{REFLO}	Ref Low	P2[4] – Bandgap (P2[4] = V _{DD} /2)	P2[4] – 1.339	P2[4] – 1.297	P2[4] – 1.244	V

Table 20. 3.3-V DC Analog Reference Specifications *(continued)*

Reference ARF_CR [5:3]	Reference Power Settings	Symbol	Reference	Description	Min	Typ	Max	Units
0b110	RefPower = high Opamp bias = high	V _{REFHI}	Ref High	2 × Bandgap	2.510	2.595	2.655	V
		V _{AGND}	AGND	Bandgap	1.276	1.301	1.332	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.006	V _{SS} + 0.031	V
	RefPower = high Opamp bias = low	V _{REFHI}	Ref High	2 × Bandgap	2.513	2.594	2.656	V
		V _{AGND}	AGND	Bandgap	1.275	1.301	1.331	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.004	V _{SS} + 0.021	V
	RefPower = medium Opamp bias = high	V _{REFHI}	Ref High	2 × Bandgap	2.516	2.595	2.657	V
		V _{AGND}	AGND	Bandgap	1.275	1.301	1.331	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.003	V _{SS} + 0.017	V
	RefPower = medium Opamp bias = low	V _{REFHI}	Ref High	2 × Bandgap	2.520	2.595	2.658	V
		V _{AGND}	AGND	Bandgap	1.275	1.300	1.331	V
		V _{REFLO}	Ref Low	V _{SS}	V _{SS}	V _{SS} + 0.002	V _{SS} + 0.015	V
0b111	All power settings. Not allowed for 3.3 V.	—	—	—	—	—	—	—

11.3.8 DC Analog PSoC Block Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, or 3.0 V to 3.6 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, respectively. Typical parameters are measured at 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 21. DC Analog PSoC Block Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
R _{CT}	Resistor unit value (continuous time)	—	12.2	—	kΩ	
C _{SC}	Capacitor unit value (switched capacitor)	—	80	—	fF	

11.3.9 DC POR and LVD Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, or 3.0 V to 3.6 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, respectively. Typical parameters are measured at 5 V or 3.3 V at 25 °C and are for design guidance only.

11.3.10 DC Programming Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, or 3.0 V to 3.6 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, respectively. Typical parameters are measured at 5 V and 3.3 V at 25°C and are for design guidance only.

Table 23. DC Programming Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
V_{DDP}	V_{DD} for programming and erase	4.5	5	5.5	V	This specification applies to the functional requirements of external programmer tools
$V_{DDL V}$	Low V_{DD} for verify	3	3.1	3.2	V	This specification applies to the functional requirements of external programmer tools
V_{DDHV}	High V_{DD} for verify	5.1	5.2	5.3	V	This specification applies to the functional requirements of external programmer tools
$V_{DDIWRITE}$	Supply voltage for flash write operation	3		5.25	V	This specification applies to this device when it is executing internal flash writes
I_{DDP}	Supply current during programming or verify	–	15	30	mA	
V_{ILP}	Input low voltage during programming or verify	–	–	0.8	V	
V_{IHP}	Input high voltage during programming or verify	2.1	–	–	V	
I_{ILP}	Input current when applying V_{ILP} to P1[0] or P1[1] during programming or verify	–	–	0.2	mA	Driving internal pull-down resistor.
I_{IHP}	Input current when applying V_{IHP} to P1[0] or P1[1] during programming or verify	–	–	1.5	mA	Driving internal pull-down resistor.
V_{OLV}	Output low voltage during programming or verify	–	–	$V_{SS} + 0.75$	V	
V_{OHV}	Output high voltage during programming or verify	$V_{DD} - 1.0$	–	V_{DD}	V	
Flash _{ENPB}	Flash endurance (per block) ^[26]	50,000	–	–	–	Erase/write cycles per block.
Flash _{ENT}	Flash endurance (total) ^[27]	1,800,000	–	–	–	Erase/write cycles.
Flash _{DR}	Flash data retention	10	–	–	Years	

11.3.11 DC I²C Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, or 3.0 V to 3.6 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, respectively. Typical parameters are measured at 5 V and 3.3 V at 25°C and are for design guidance only.

Table 24. DC I²C Specifications^[28]

Symbol	Description	Min	Typ	Max	Units	Notes
V_{ILI2C}	Input low level	–	–	$0.3 \times V_{DD}$	V	$3.0\text{ V} \leq V_{DD} \leq 3.6\text{ V}$
		–	–	$0.25 \times V_{DD}$	V	$4.75\text{ V} \leq V_{DD} \leq 5.25\text{ V}$
V_{IHI2C}	Input high level	$0.7 \times V_{DD}$	–	–	V	$3.0\text{ V} \leq V_{DD} \leq 5.25\text{ V}$

11.4.8 AC Analog Output Buffer Specifications

The following tables list guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, or 3.0 V to 3.6 V and $-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$, respectively. Typical parameters are measured at 5 V and 3.3 V at 25°C and are for design guidance only.

Table 33. 5-V AC Analog Output Buffer Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
t_{ROB}	Rising settling time to 0.1%, 1 V Step, 100 pF load	–	–	2.5	μs	
	Power = low Power = high	– –	– –	2.5 2.5	μs μs	
t_{SOB}	Falling settling time to 0.1%, 1 V Step, 100 pF load	–	–	2.2	μs	
	Power = low Power = high	– –	– –	2.2 2.2	μs μs	
SR_{ROB}	Rising slew rate (20% to 80%), 1 V Step, 100 pF load	0.65	–	–	V/ μs	
	Power = low Power = high	0.65 0.65	– –	– –	V/ μs V/ μs	
SR_{FOB}	Falling slew rate (80% to 20%), 1 V Step, 100 pF load	0.65	–	–	V/ μs	
	Power = low Power = high	0.65 0.65	– –	– –	V/ μs V/ μs	
BW_{OBSS}	Small signal bandwidth, 20 mV _{pp} , 3 dB BW, 100 pF load	0.8	–	–	MHz	
	Power = low Power = high	0.8 0.8	– –	– –	MHz MHz	
BW_{OBSL}	Large signal bandwidth, 1 V _{pp} , 3 dB BW, 100 pF load	300	–	–	kHz	
	Power = low Power = high	300 300	– –	– –	kHz kHz	

Table 34. 3.3-V AC Analog Output Buffer Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
t_{ROB}	Rising settling time to 0.1%, 1 V Step, 100 pF load	–	–	3.8	μs	
	Power = low Power = high	– –	– –	3.8 3.8	μs μs	
t_{SOB}	Falling settling time to 0.1%, 1 V Step, 100 pF load	–	–	2.6	μs	
	Power = low Power = high	– –	– –	2.6 2.6	μs μs	
SR_{ROB}	Rising slew rate (20% to 80%), 1 V Step, 100 pF load	0.5	–	–	V/ μs	
	Power = low Power = high	0.5 0.5	– –	– –	V/ μs V/ μs	
SR_{FOB}	Falling slew rate (80% to 20%), 1 V Step, 100 pF load	0.5	–	–	V/ μs	
	Power = low Power = high	0.5 0.5	– –	– –	V/ μs V/ μs	
BW_{OBSS}	Small signal bandwidth, 20 mV _{pp} , 3dB BW, 100 pF load	0.7	–	–	MHz	
	Power = low Power = high	0.7 0.7	– –	– –	MHz MHz	
BW_{OBSL}	Large signal bandwidth, 1 V _{pp} , 3dB BW, 100 pF load	200	–	–	kHz	
	Power = low Power = high	200 200	– –	– –	kHz kHz	

11.4.9 AC Programming Specifications

The following table lists guaranteed maximum and minimum specifications for the voltage and temperature ranges: 4.75 V to 5.25 V and $-40\text{ }^{\circ}\text{C} \leq T_A \leq 85\text{ }^{\circ}\text{C}$, or 3.0 V to 3.6 V and $-40\text{ }^{\circ}\text{C} \leq T_A \leq 85\text{ }^{\circ}\text{C}$, respectively. Typical parameters are measured at 5 V and 3.3 V at 25 °C and are for design guidance only.

Table 35. AC Programming Specifications

Symbol	Description	Min	Typ	Max	Units	Notes
t_{RSCLK}	Rise time of SCLK	1	–	20	ns	
t_{FSCLK}	Fall time of SCLK	1	–	20	ns	
t_{SSCLK}	Data setup time to falling edge of SCLK	40	–	–	ns	
t_{HSCLK}	Data hold time from falling edge of SCLK	40	–	–	ns	
F_{SCLK}	Frequency of SCLK	0	–	8	MHz	
t_{ERASEB}	Flash erase time (block)	–	10	–	ms	
t_{WRITE}	Flash block write time	–	40	–	ms	
t_{DSCLK}	Data out delay from falling edge of SCLK	–	–	45	ns	$V_{\text{DD}} > 3.6$
t_{DSCLK3}	Data out delay from falling edge of SCLK	–	–	50	ns	$3.0 \leq V_{\text{DD}} \leq 3.6$
t_{ERASEALL}	Flash erase time (bulk)	–	40	–	ms	Erase all blocks and protection fields at once
$t_{\text{PROGRAM_HOT}}$	Flash block erase + flash block write time	–	–	100 ^[34]	ms	$0\text{ }^{\circ}\text{C} \leq T_j \leq 100\text{ }^{\circ}\text{C}$
$t_{\text{PROGRAM_COLD}}$	Flash block erase + flash block write time	–	–	200 ^[34]	ms	$-40\text{ }^{\circ}\text{C} \leq T_j \leq 0\text{ }^{\circ}\text{C}$

Note

34. For the full industrial range, the user must employ a temperature sensor user module (FlashTemp) and feed the result to the temperature argument before writing. See the Flash APIs application note [Design Aids – Reading and Writing PSoC® Flash – AN2015](#) for more information.

11.5 Thermal Impedance

Table 37. Thermal Impedances per Package

Package	Typical θ_{JA} ^[36]
56-Pin QFN ^[37]	12.93 °C/W
68-Pin QFN ^[37]	13.05 °C/W
100-Ball VFBGA	65 °C/W
100-Pin TQFP	51 °C/W

11.6 Solder Reflow Peak Specifications

Table 38 shows the solder reflow temperature limits that must not be exceeded.

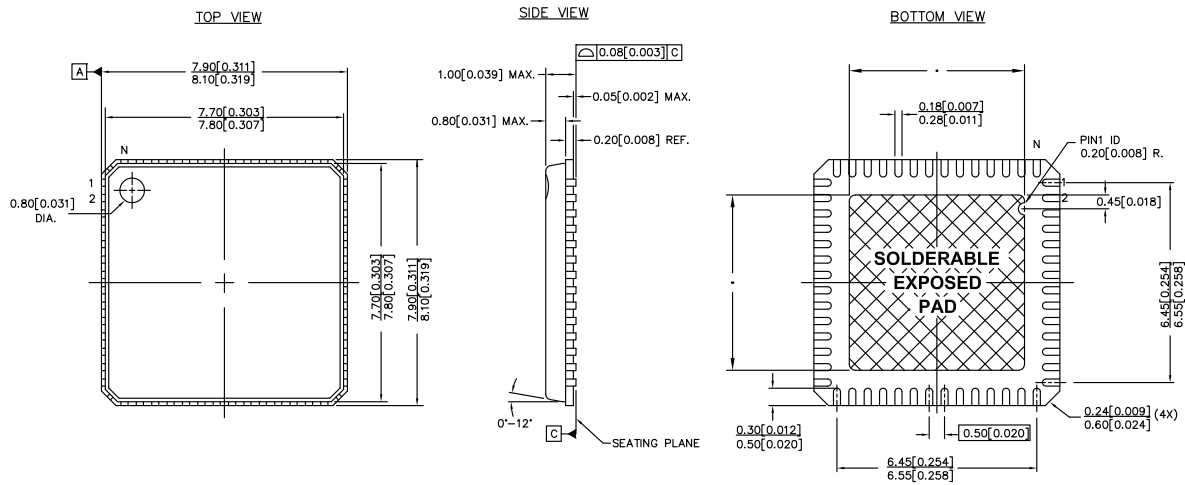
Table 38. Solder Reflow Specifications

Package	Maximum Peak Temperature (T_C)	Maximum Time above $T_C - 5$ °C
56-Pin QFN	260 °C	30 seconds
68-Pin QFN	260 °C	30 seconds
100-Ball VFBGA	260 °C	30 seconds
100-Pin TQFP	260 °C	30 seconds

Notes

36. $T_J = T_A + \text{POWER} \times \theta_{JA}$

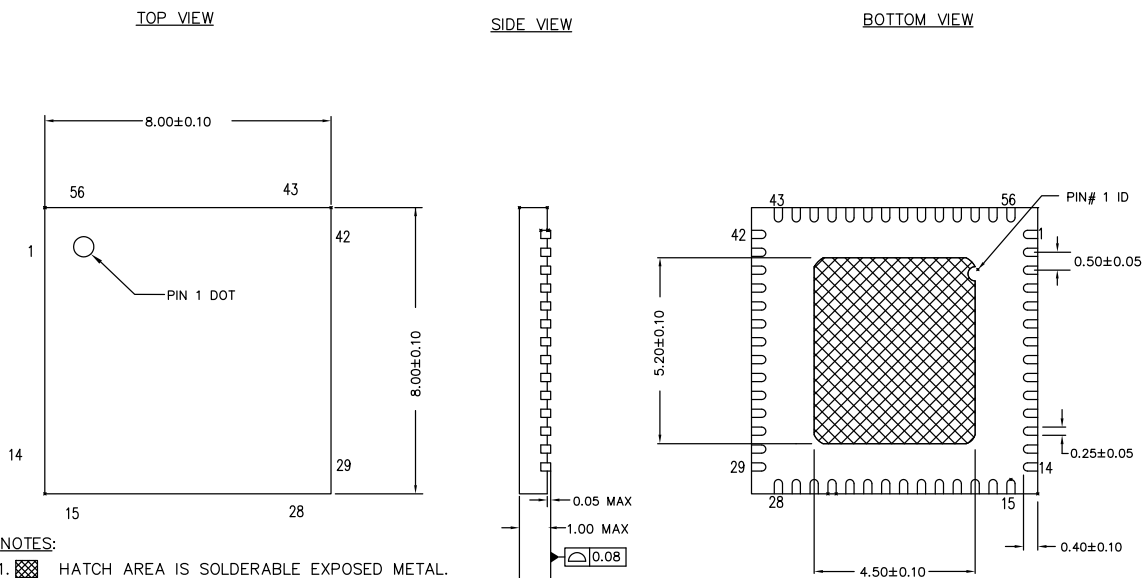
37. To achieve the thermal impedance specified for the QFN package, see the *Application Notes for Surface Mount Assembly of Amkor's MicroLeadFrame (MLF) Packages* available at <http://www.amkor.com>.

Figure 17. 56-pin QFN ($8 \times 8 \times 1.0$ mm) LF56A/LY56A 4.5×5.21 E-Pad (Subcon Punch Type Pkg.) Package Outline, 001-12921

NOTES:

1.  HATCH AREA IS SOLDERABLE EXPOSED METAL.
2. REFERENCE JEDEC#: MO-220
3. PACKAGE WEIGHT: 0.162g
4. ALL DIMENSIONS ARE IN MM [MIN/MAX]
5. PACKAGE CODE

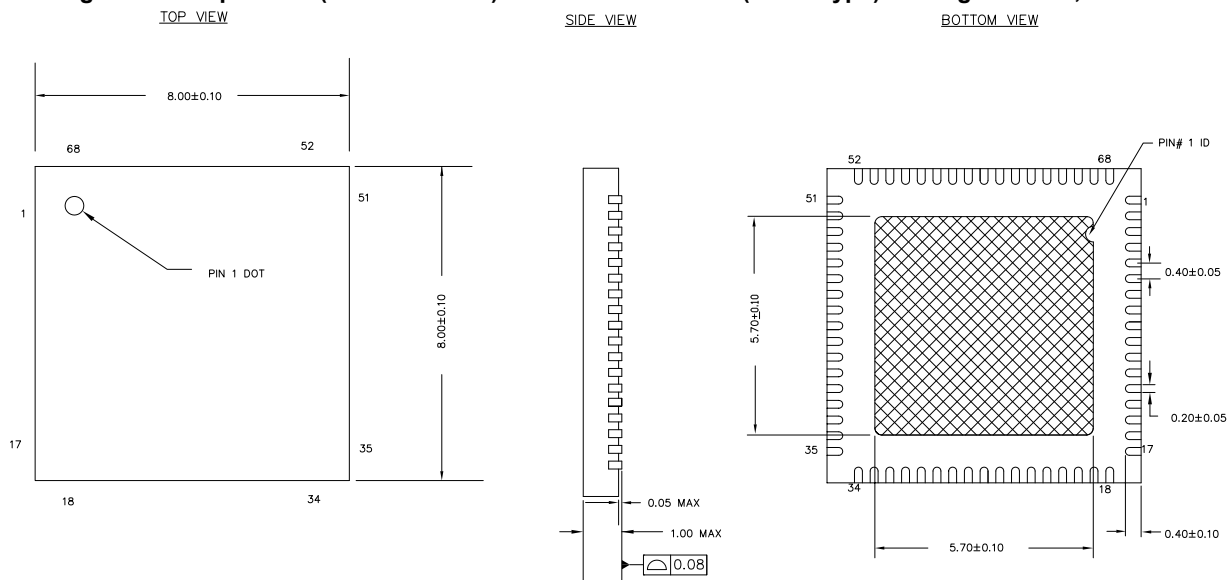
PART #	DESCRIPTION
LF56A	STANDARD
LY56A	PB-FREE

001-12921 *C

Figure 18. 56-pin QFN ($8 \times 8 \times 1.0$ mm) LT56B 4.5×5.2 E-Pad (Sawn) Package Outline, 001-53450

NOTES:

1.  HATCH AREA IS SOLDERABLE EXPOSED METAL.
2. REFERENCE JEDEC#: MO-220
3. PACKAGE WEIGHT: 162 ± 16 mg
4. ALL DIMENSIONS ARE IN MILLIMETERS

001-53450 *D

Figure 19. 68-pin QFN (8 × 8 × 1.0 mm) LT68 5.7 × 5.7 E-Pad (Sawn Type) Package Outline, 001-09618

NOTES:

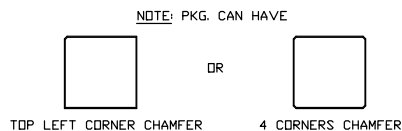
1.  HATCH AREA IS SOLDERABLE EXPOSED METAL.
2. REFERENCE JEDEC#: MO-220
3. PACKAGE WEIGHT: 17 ± 2mg
4. ALL DIMENSIONS ARE IN MILLIMETERS

001-09618 *E

[illegible]

2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE
BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH

3. DIMENSIONS IN MILLIMETERS



- For information on the preferred dimensions for mounting QFN packages, see the Application Note, *Application Notes for Surface Mount Assembly of Amkor's MicroLeadFrame (MLF) Packages* available at <http://www.amkor.com>.
- Pinned vias for thermal conduction are not required for the low power PSoC device.

15. Acronyms

15.1 Acronyms Used

The following table lists the acronyms that are used in this document.

Acronym	Description	Acronym	Description
AC	alternating current	MIPS	million instructions per second
ADC	analog-to-digital converter	OCD	on-chip debug
API	application programming interface	PCB	printed circuit board
CMOS	complementary metal oxide semiconductor	PDIP	plastic dual-in-line package
CPU	central processing unit	PGA	programmable gain amplifier
CRC	cyclic redundancy check	POR	power-on reset
CT	continuous time	PPOR	precision power-on reset
DAC	digital-to-analog converter	PRS	pseudo-random sequence
DC	direct current	PSoC [®]	Programmable System-on-Chip [™]
DTMF	dual-tone multi-frequency	PWM	pulse-width modulator
EEPROM	electrically erasable programmable read-only memory	QFN	quad flat no leads
GPIO	general purpose I/O	SAR	successive approximation register
ICE	in-circuit emulator	SC	switched capacitor
IDE	integrated development environment	SLIMO	slow IMO
ILO	internal low-speed oscillator	SOIC	small-outline integrated circuit
IMO	internal main oscillator	SPI [™]	serial peripheral interface
I/O	input/output	SRAM	static random-access memory
IrDA	infrared data association	SROM	supervisory read-only memory
ISSP	In-System Serial Programming	TQFP	thin quad flat pack
LCD	liquid crystal display	UART	universal asynchronous receiver / transmitter
LED	light-emitting diode	USB	universal serial bus
LPC	low power comparator	VFBGA	very fine-pitch ball grid array
LVD	low-voltage detect	WDT	watchdog timer
MAC	multiply-accumulate	XRES	external reset
MCU	microcontroller unit		

17. Glossary *(continued)*

SRAM	An acronym for static random access memory. A memory device allowing users to store and retrieve data at a high rate of speed. The term static is used because, after a value has been loaded into an SRAM cell, it remains unchanged until it is explicitly altered or until power is removed from the device.
SROM	An acronym for supervisory read only memory. The SROM holds code that is used to boot the device, calibrate circuitry, and perform Flash operations. The functions of the SROM may be accessed in normal user code, operating from Flash.
stop bit	A signal following a character or block that prepares the receiving device to receive the next character or block.
synchronous	1. A signal whose data is not acknowledged or acted upon until the next active edge of a clock signal. 2. A system whose operation is synchronized by a clock signal.
tristate	A function whose output can adopt three states: 0, 1, and Z (high-impedance). The function does not drive any value in the Z state and, in many respects, may be considered to be disconnected from the rest of the circuit, allowing another output to drive the same net.
UART	A UART or universal asynchronous receiver-transmitter translates between parallel bits of data and serial bits.
user modules	Pre-build, pre-tested hardware/firmware peripheral functions that take care of managing and configuring the lower level Analog and Digital PSoC Blocks. User Modules also provide high level API (Application Programming Interface) for the peripheral function.
user space	The bank 0 space of the register map. The registers in this bank are more likely to be modified during normal program execution and not just during initialization. Registers in bank 1 are most likely to be modified only during the initialization phase of the program.
V _{DD}	A name for a power net meaning "voltage drain." The most positive power supply signal. Usually 5 V or 3.3 V.
V _{SS}	A name for a power net meaning "voltage source." The most negative power supply signal.
watchdog timer	A timer that must be serviced periodically. If it is not serviced, the CPU resets after a specified period of time.

3. PMA Index Register fails to auto-increment with CPU_Clock set to SysClk/1 (24 MHz).

■ PROBLEM DEFINITION

When the device is operating at 4.75 to 5.25 V and the CPU_Clock is set to SysClk/1 (24 MHz), the USB PMA Index Register may fail to increment automatically when used in an OUT endpoint configuration at Full-Speed. When the application program attempts to use the bReadOutEP() function the first byte in the PMA buffer is always returned.

■ TRIGGER CONDITION(S)

An internal flip-flop hold problem associated with Index Register increment function. All reads of the associated RAM originate from the first byte. The hold problem has no impact on other circuits or functions within the device.

■ WORKAROUND

To make certain that the index register properly increments, set the CPU_Clock to SysClk/2 (12 MHz) during the read of the PMA buffer. An example for the clock adjustment method is listed below.

PSoC Designer™ 4.3 User Module workaround: PSoC Designer Release 4.3 and subsequent releases includes a revised full-speed USB User Module with the revised firmware work-around included (see example below).

```
;;
;; 24 MHz read PMA workaround
;;
M8C_SetBank1
mov A, reg[OSC_CR0]
push A
and A, 0xf8 ;clear the clock bits (briefly chg the cpu_clk to 3 MHz)
or A, 0x02 ;will set clk to 12Mhz

mov reg[OSC_CR0],A ;clk is now set at 12 MHz
M8C_SetBank0
.loop:
  mov A, reg[PMA0_DR] ; Get the data from the PMA space
  mov [X], A ; save it in data array
  inc X ; increment the pointer
  dec [USB_APITemp+1] ; decrement the counter
  jnz .loop ; wait for count to zero out
;;
;; 24MHz read PMA workaround (back to previous clock speed)
;;
pop A ;recover previous reg[OSC_CR0] value
M8C_SetBank1
mov reg[OSC_CR0],A ;clk is now set at previous value
M8C_SetBank0
;;
;; end 24Mhz read PMA workaround
```